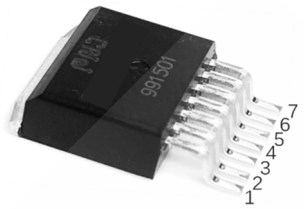
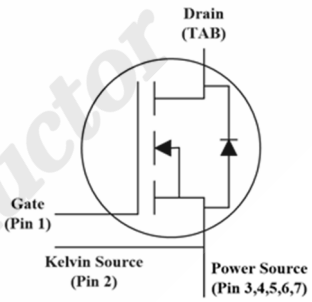
SiC MOS P3M12040G7

N-Channel Enhancement Mode



Features

- Qualified to AEC-Q101
- High Blocking Voltage with Low On-Resistance
- High-Frequency Operation
- Ultra-Small Q_{gd}
- 100% UIS tested



Benefits

- Improve System Efficiency
- Increase Power Density
- Reduce Heat Sink Requirements
- Reduction of System Cost

TO-263-7

Drain	TAB
Gate	1
Kelvin Source	2
Power Source	3~7

Applications

- Solar Inverters
- EV Battery Chargers
- High Voltage DC/DC Converters
- Switch Mode Power Supplies

RoHS

Halogen

Order Information

Part Number	Package	Marking
P3M12040G7	TO-263-7	P3M12040G7

Contents

1. Maximum Ratings

At T_J= 25℃, unless specified otherwise

Parameter	Symbol	Value	Unit	Test Conditions
Drain - Source Voltage	V_{DSmax}	1200	V	V_{GS} = 0V I_D = 100μA
Gate - Source Voltage (dynamic)	V_{GSmax}	-8 / +21	V	AC (f >1Hz)
Gate - Source Voltage(static) turn-on gate voltage turn-off gate voltage	$V_{GS,on}$ $V_{GS,off}$	+15 / +18 -3	V	Static
Continuous Drain Current	I_D	63	A	V_{GS} = 15V T_C = 25℃
		44		V_{GS} = 15V T_C = 100℃
Power Dissipation	P_D	349	W	
Operating Junction	T_J	-55 To +175	℃	
Storage Temperature	T_{stg}	-55 To +175	℃	
Solder Temperature	T_L	260	℃	

2. Electrical Characteristics

At T_J= 25℃, unless specified otherwise

Parameter	Symbol	Value			Unit	Test Conditions
		Min.	Typ.	Max.		
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	1200	/	/	V	V_{GS}= 0V I_D= 100μA
Gate Threshold Voltage	$V_{GS(th)}$	1.8	2.4	/	V	(tested after 30ms pulse at V_{GS}=15V) V_{DS}= V_{GS} I_D= 10mA T_J = 25℃
		/	1.6	/	V	V_{DS}= V_{GS} I_D= 10mA T_J = 175℃
Reverse Bias Drain Current	I_{DSS}	/	1	100	μA	V_{GS}=0V V_{DS}=1200V
Gate-Source Leakage Current	I_{GSS}	/	20	250	nA	V_{GS}= 15V V_{DS}= 0V
Drain-Source On-State Resistance	$R_{DS(on)}$	/	40	52	mΩ	V_{GS}= 15V I_D= 40A T_J = 25℃
		/	59	/		V_{GS}= 15V I_D= 40A T_J = 175℃
		/	35	/		V_{GS}= 18V I_D= 40A T_J = 25℃
Transconductance	g_{fs}	/	21	/	S	V_{DS}= 20V I_{DS}= 40A T_J = 25℃
		/	20	/		V_{DS}= 20V I_{DS}= 40A T_J= 175℃

Parameter	Symbol	Value			Unit	Test Conditions
		Min.	Typ.	Max.		
Input Capacitance	C_{iss}	/	3505	/	pF	V_{GS}= 0V V_{DS}= 800V f= 1MHz V_{AC}= 25mV
Output Capacitance	C_{oss}	/	125.6	/		
Reverse Transfer Capacitance	C_{rss}	/	5.4	/		
Coss Stored Energy	E_{oss}	/	59.3	/	μJ	
Turn-on Energy	E_{on}	/	654.1	/	μJ	V_{DS}= 800V V_{GS}= -3/15V I_D= 40A R_G= 1Ω
Turn-off Energy	E_{off}	/	96.7	/		
Turn-on Energy	E_{on}	/	520.3	/	μJ	V_{DS}= 800V V_{GS}= -3/18V I_D= 40A R_G= 1Ω
Turn-off Energy	E_{off}	/	92.7	/		
Turn-On Delay Time	$t_{d(on)}$	/	17.1	/	ns	V_{DS}= 800V V_{GS}= -3/15V I_D= 40A R_G= 1Ω
Rise Time	t_r	/	25.1	/		
Turn-Off Delay Time	$t_{d(off)}$	/	30.2	/		
Fall Time	t_f	/	15.7	/		
Internal Gate Resistance	$R_{G(int)}$	/	1.3	/	Ω	f= 1MHz V_{AC}= 25mV
Gate to Source Charge	Q_{gs}	/	38	/	nC	V_{DS} =800V I_{DS}= 40A

Parameter	Symbol	Value			Unit	Test Conditions
		Min.	Typ.	Max.		
Gate to Drain Charge	Q_{gd}	/	19	/		V_{GS}= -3/15V I_G= 5mA
Total Gate Charge	Q_g	/	98	/		

3. Reverse Diode Characteristics

At T_J= 25℃, unless specified otherwise

Parameter	Symbol	Value		Unit	Test Conditions
		Typ.	Max.		
Diode Forward Voltage	V_{SD}	5.2	/	V	V_{GS}= -3V I_{SD}= 20A T_J= 25℃
		4.9	/	V	V_{GS}= -3V I_{SD}= 20A T_J= 175℃
Continuous Diode Forward Current	I_S	51	/	A	V_{GS}= -3V
Reverse Recover Time	t_{rr}	16.3	/	ns	V_{GS}= -3V I_{SD}= 40A V_R= 800V d_{if}/d_t= 5100A/μs T_J= 25℃
Reverse Recovery Charge	Q_{rr}	528.0	/	nC	
Peak Reverse Recovery Current	I_{rrm}	51.6	/	A	

4. Thermal Characteristics

Parameter	Symbol	Value	Unit
Thermal Resistance from Junction to Case	$R_{\theta JC}$	0.43	℃/W

5. Typical Performance

At T_J= 25℃, unless specified otherwise

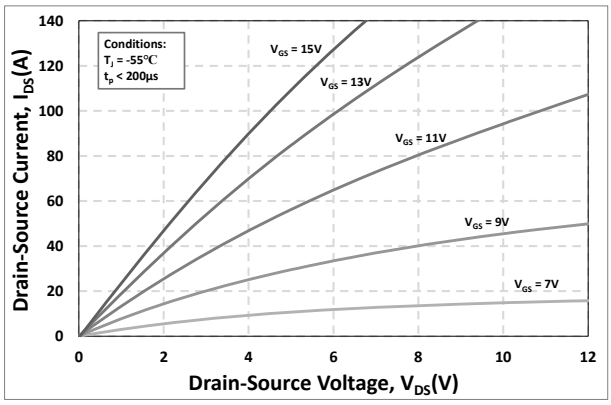


Figure 1. Output Characteristics T_J = -55℃

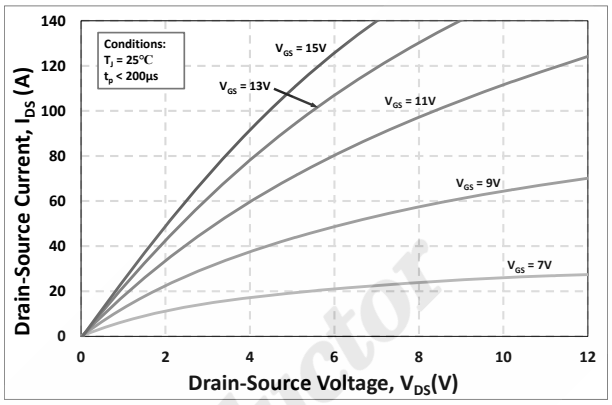


Figure 2. Output Characteristics T_J = 25℃

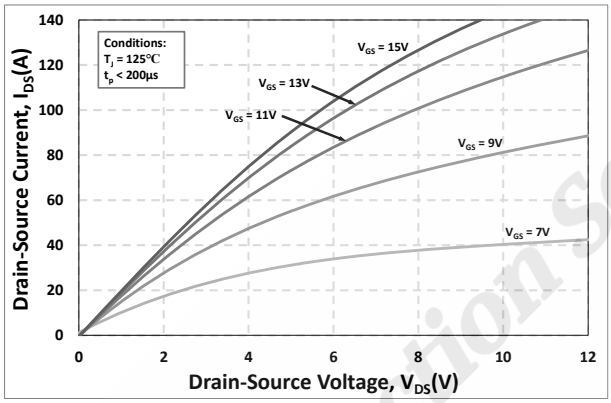


Figure 3. Output Characteristics T_J = 125℃

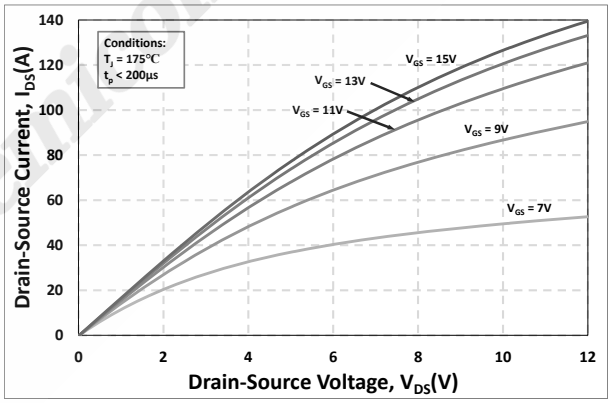


Figure 4. Output Characteristics T_J = 175℃

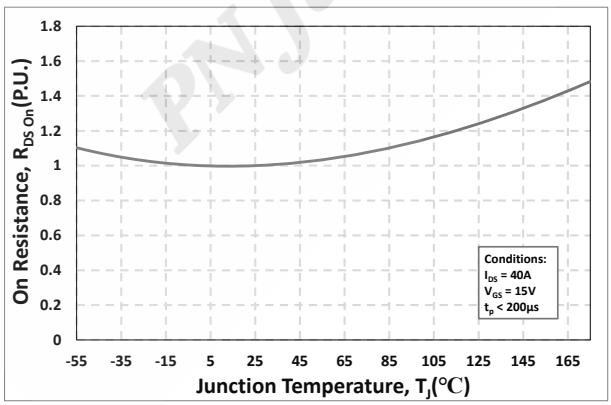


Figure 5. Normalized On-Resistance vs. Temperature

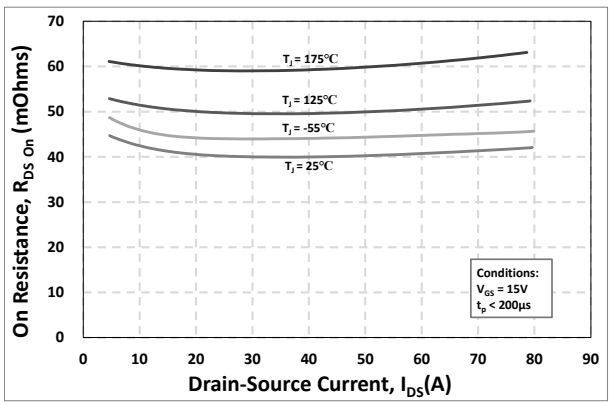


Figure 6. On-Resistance vs. Drain Current Various Temperatures

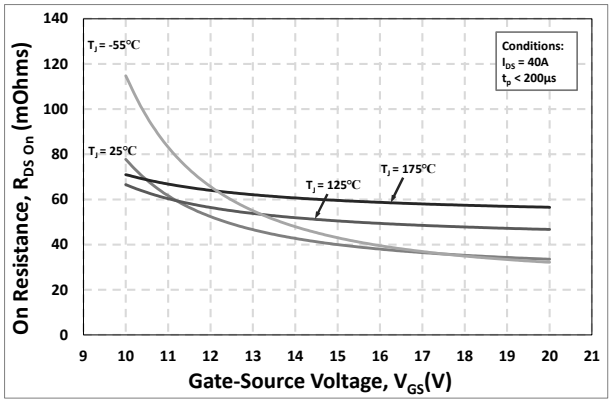


Figure 7. On-Resistance vs. Gate-Source Voltage

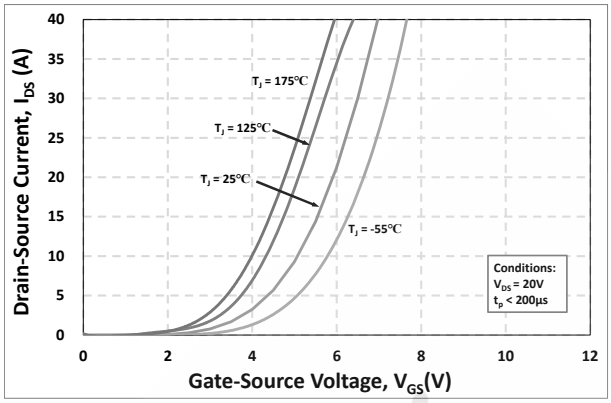


Figure 8. Transfer Characteristic for Various Junction Temperatures

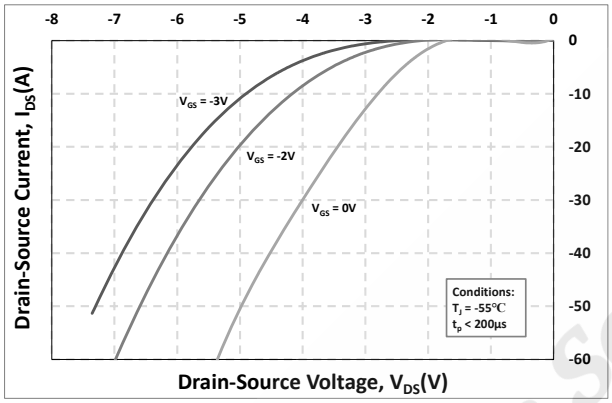


Figure 9. Body Diode Characteristic at -55°C

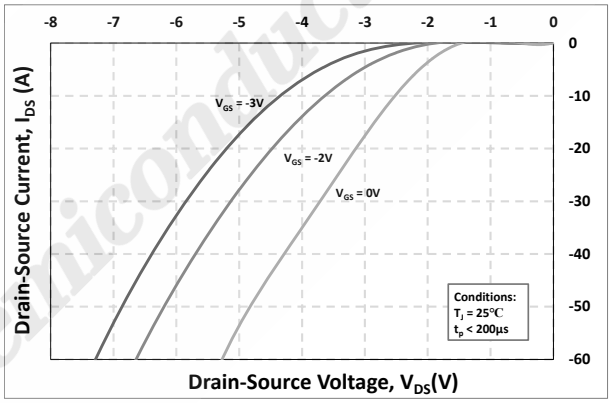


Figure 10. Body Diode Characteristic at 25°C

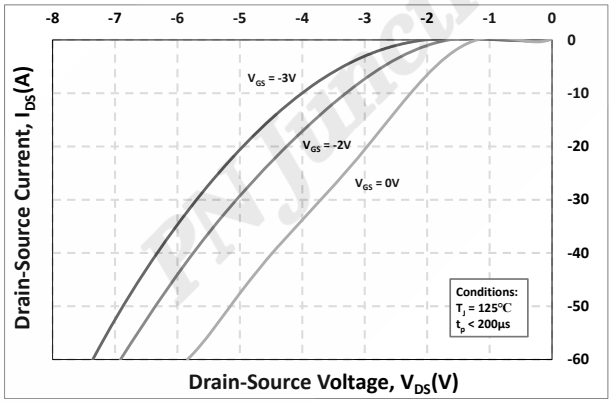


Figure 11. Body Diode Characteristic at 125°C

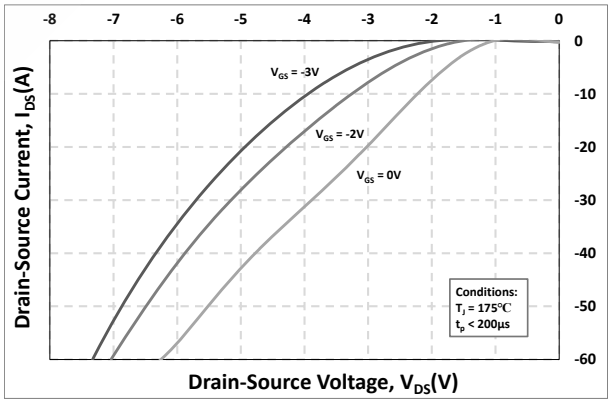


Figure 12. Body Diode Characteristic at 175°C

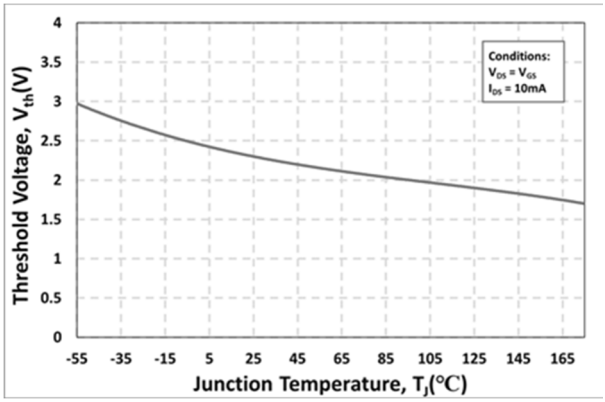


Figure 13. Threshold Voltage vs. Temperature

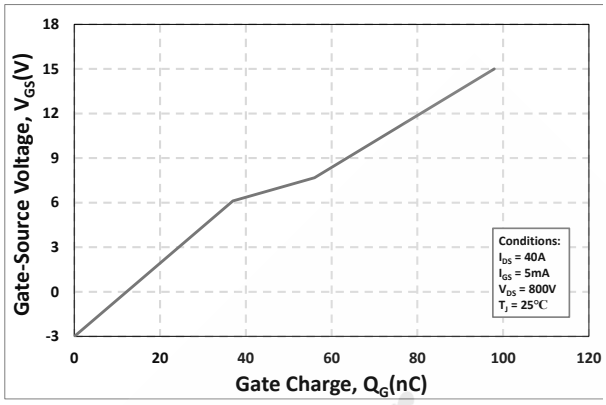


Figure 14. Gate Charge Characteristics

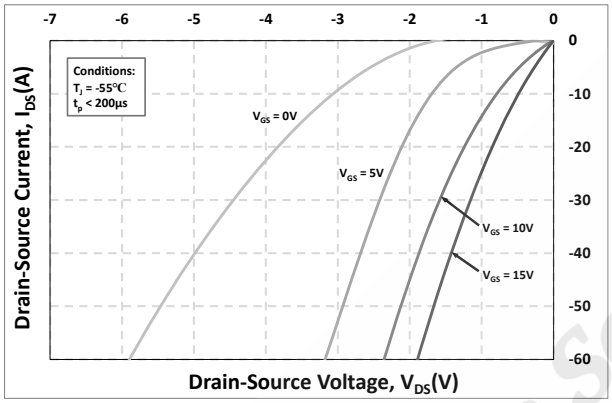


Figure 15. 3rd Quadrant Characteristic at -55°C

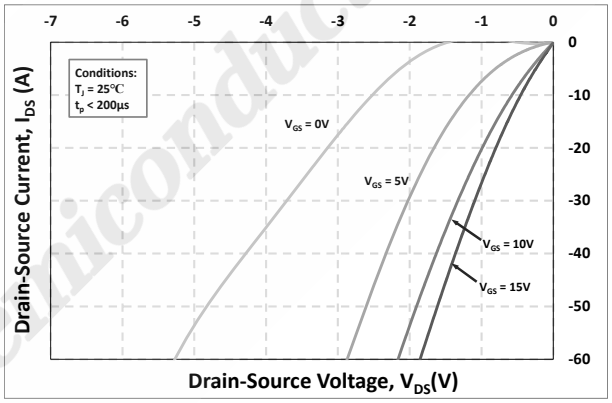


Figure 16. 3rd Quadrant Characteristic at 25°C

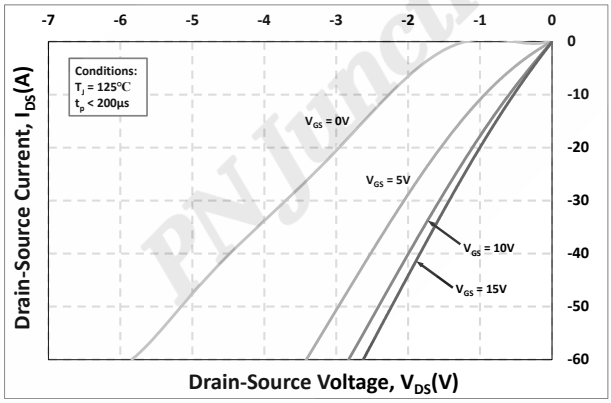


Figure 17. 3rd Quadrant Characteristic at 125°C

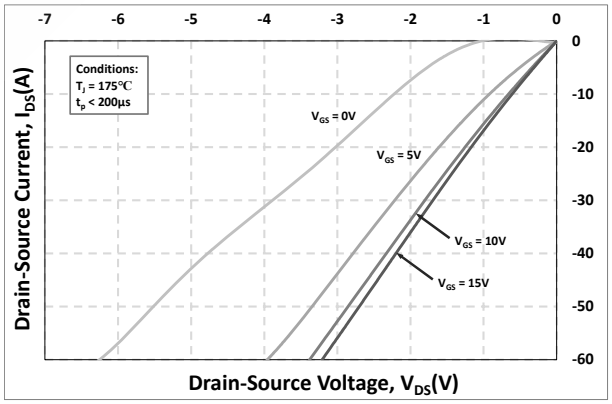


Figure 18. 3rd Quadrant Characteristic at 175°C

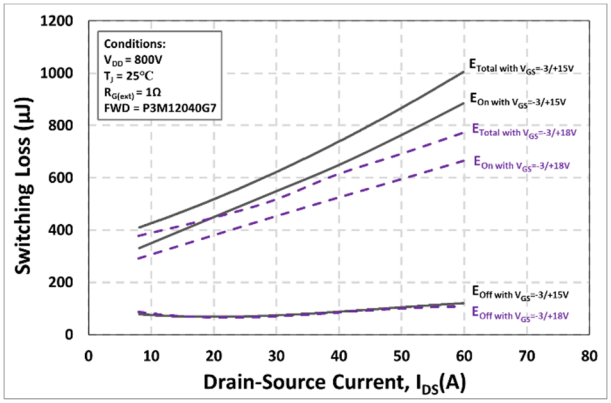


Figure 19. Clamped Inductive Switching Energy vs. Drain Current (V_{DD}= 800V)

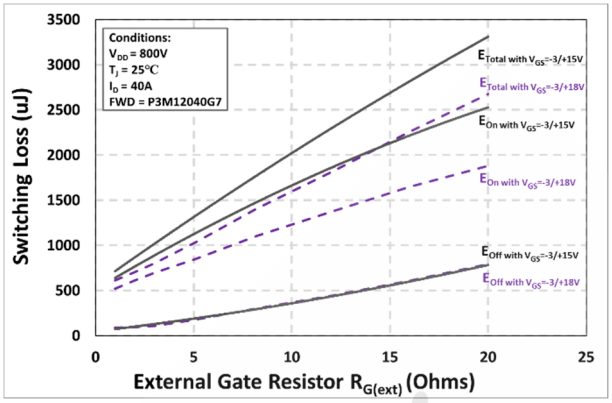


Figure 20. Clamped Inductive Switching Energy vs. $R_{G(ext)}$

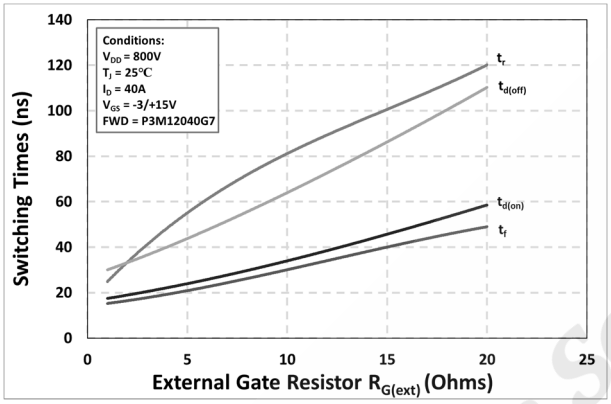


Figure 21. Switching Times vs. $R_{G(ext)}$

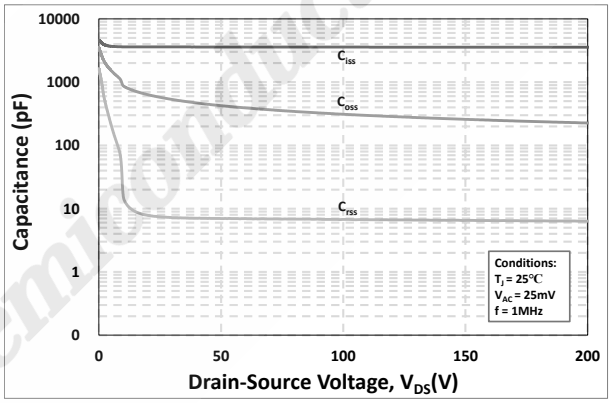


Figure 22. Capacitances vs. Drain-Source Voltage (0 - 200V)

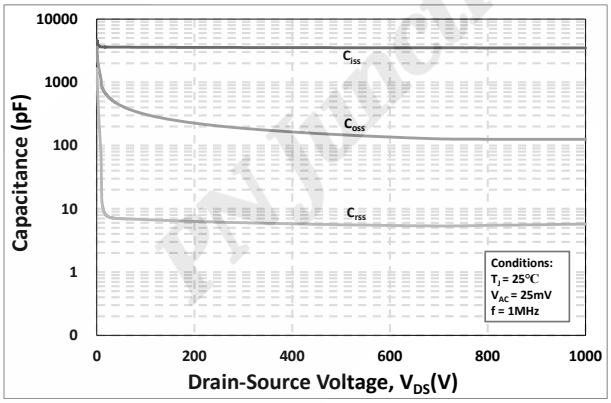


Figure 23. Capacitances vs. Drain-Source Voltage (0 - 1000V)

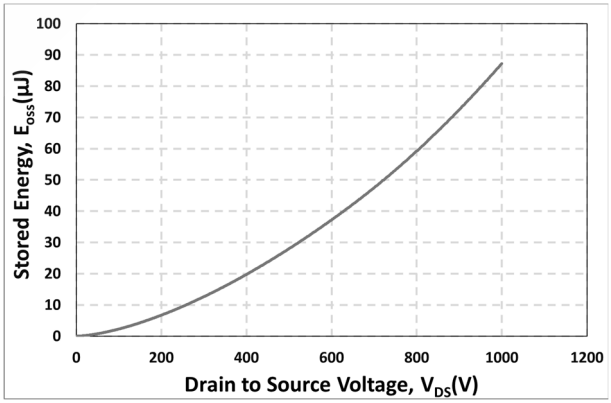


Figure 24. Output Capacitor Stored Energy

6. Definitions

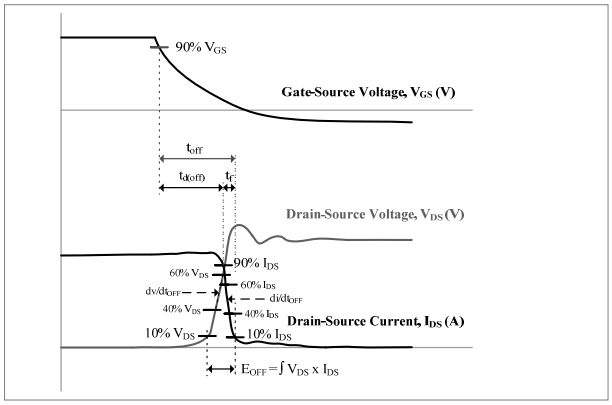


Figure 25. Turn-off Transient Definitions

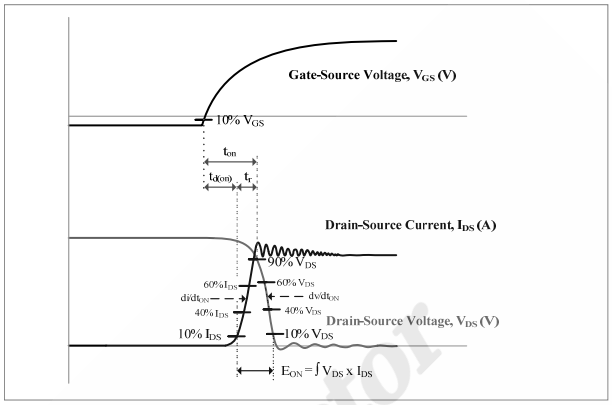


Figure 26. Turn-on Transient Definitions

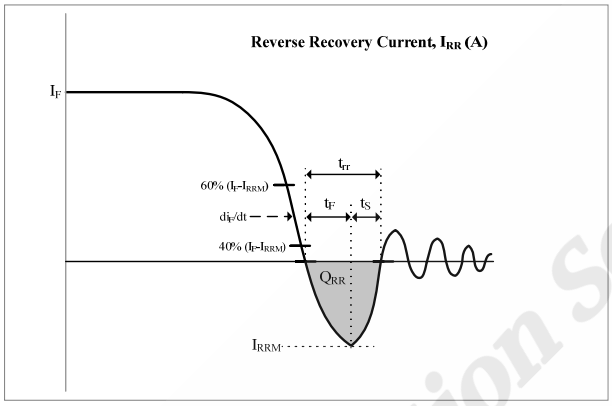


Figure 27. Reverse Recovery Definitions

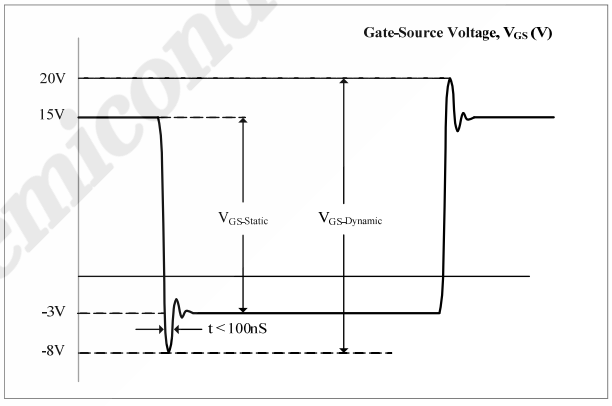
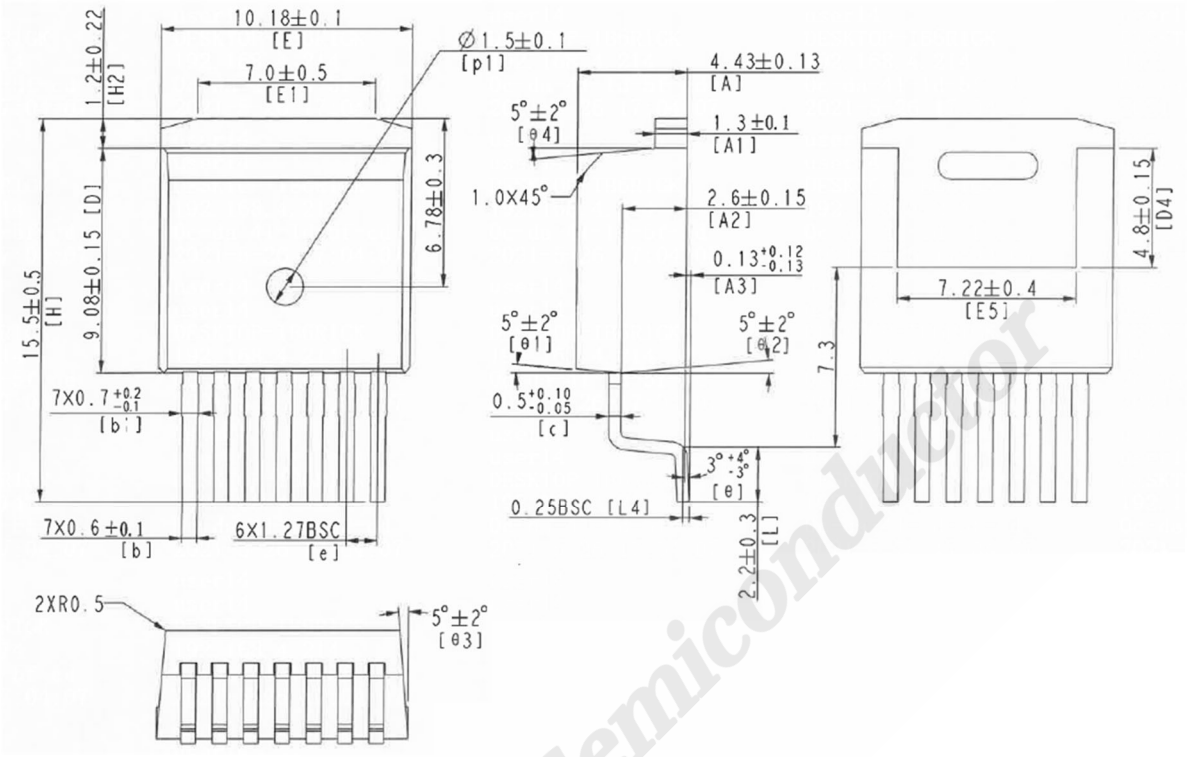


Figure 28. Vgs Transient Definitions

7. Package Outlines



Drawing and Dimensions

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